

BYC30MX-650P

Hyperfast power diode Rev.01 - 16 September 2022

**Product data sheet** 

#### **1. General description**

Hyperfast power diode in a 2-lead TO220F plastic package.



#### 2. Features and benefits

- Excellent avalanche energy robustness
- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

#### 3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

# 4. Quick reference data

Symbol	Parameter	Conditions	Notes	s Values			Unit
Absolute	maximum rating						
V <sub>RRM</sub>	repetitive peak reverse voltage				650		V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; Fig. 1; Fig. 2		30			А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_{\rm p}$ = 25 $\mu s;$ square-wave pulse			60		A
I <sub>FSM</sub> non-repetitive peak forward current		$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3		270			A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			297		А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	2.05	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.38	1.80	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 6</u>		-	20	24	ns

## 5. Pinning information

Table 2. F	inning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode	000	K — A 001aaa020
mb	mb	mounting base; connected to cathod		

## 6. Ordering information

Table 3. Ordering information									
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date			
BYC30MX-650P	TO220F-2L	BYC30MX-650PQ	Tube	50	TO220Fd-2L	02-Aug-2022			

### 7. Marking

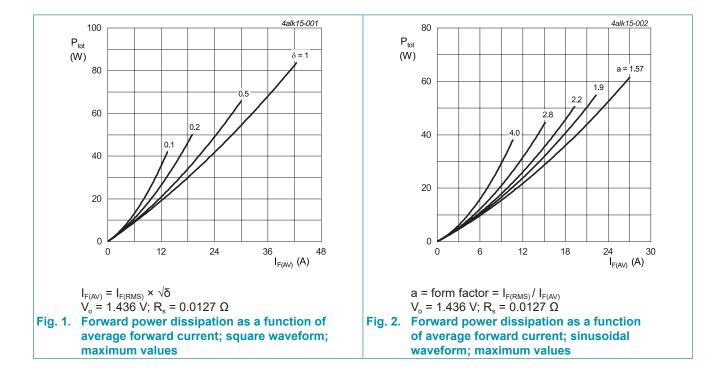
Table 4. Marking codes		
Type number	Marking codes	
BYC30MX-650P	BYC30MX 650P	

#### 8. Limiting values

#### Table 5. Limiting values

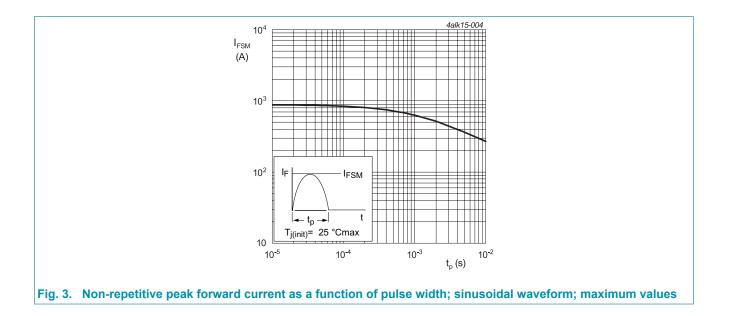
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>		30	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_{\rm p}$ = 25 $\mu s$ ; square-wave pulse		60	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3		270	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297	А
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



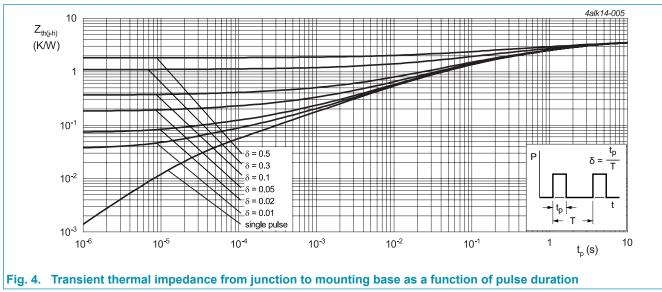
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#### BYC30MX-650P Hyperfast power diode



### 9. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 4</u>		-	-	3.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

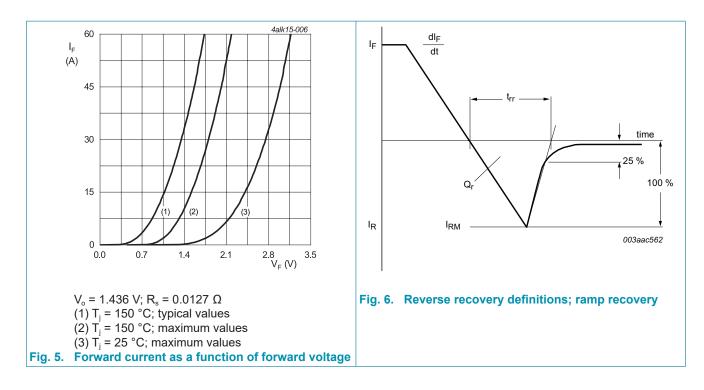


### 10. Isolation characteristics

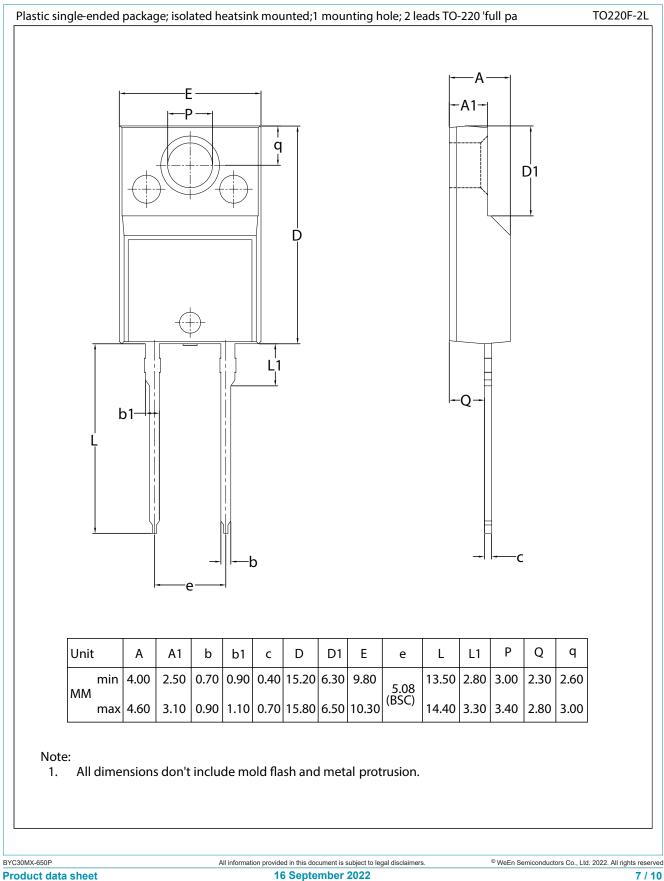
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

### **11. Characteristics**

	haracteristics			1			
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	2.05	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.38	1.80	V
I <sub>R</sub> revers	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.6	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.25	1	mA
Dynamic	characteristics	1		,			
Q <sub>r</sub>	reverse charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 6}$		-	68	-	nC
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>		-	330	-	nC
t <sub>rr</sub> r	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	20	24	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 6}$		-	38	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>		-	73	-	ns
cur	peak reverse recovery currentnon-repetitive	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 6}$		-	3.7	-	A
	avalanche energy	I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>		-	9.1	-	A
E <sub>as</sub>	non-repetitive avalanche energy	I <sub>R</sub> = 2 A; L = 15 mH; T <sub>j(init)</sub> = 25 °C		30	-	-	mJ



### 12. Package outline



# BYC30MX-650P

#### Hyperfast power diode

### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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